

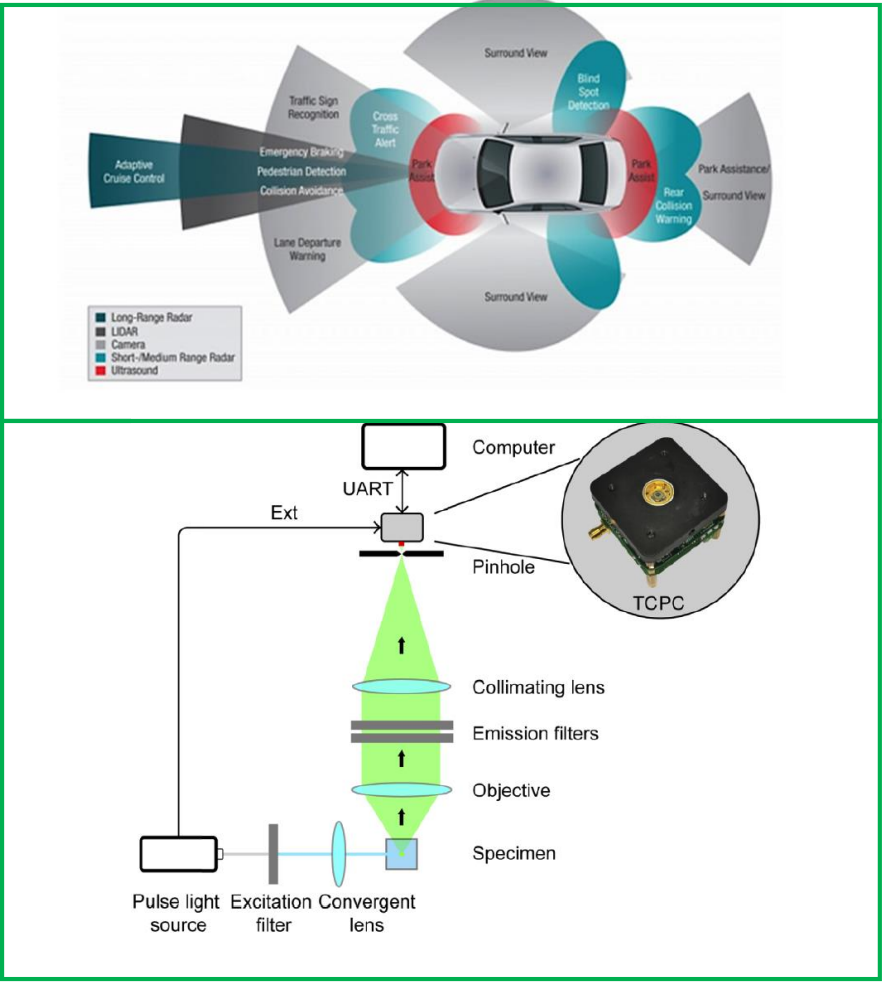
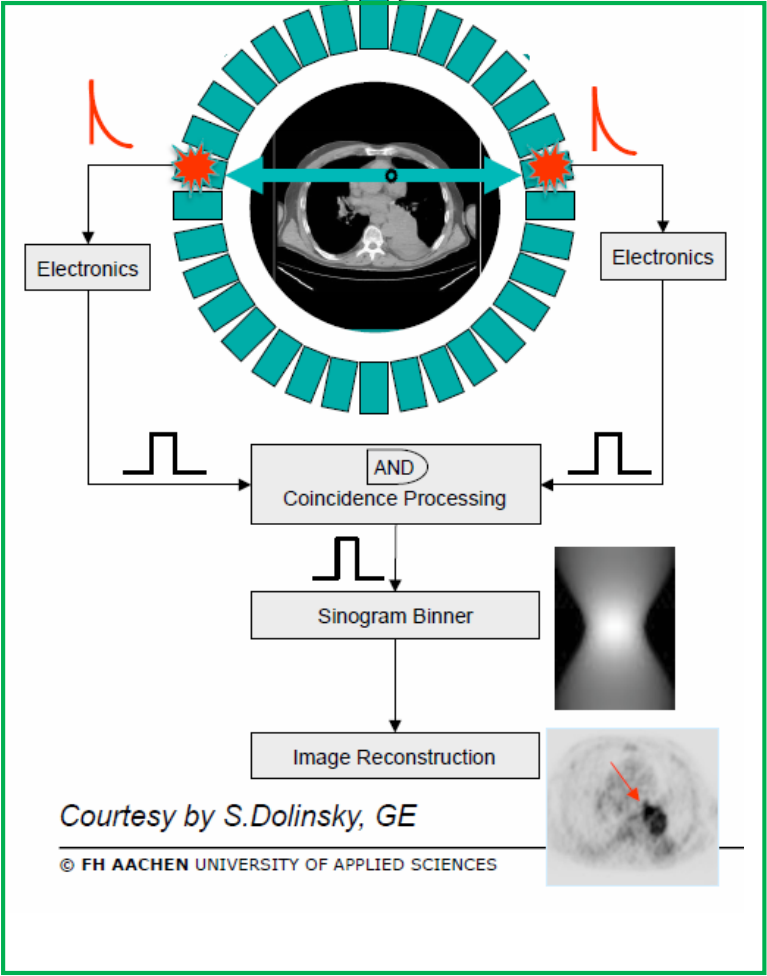
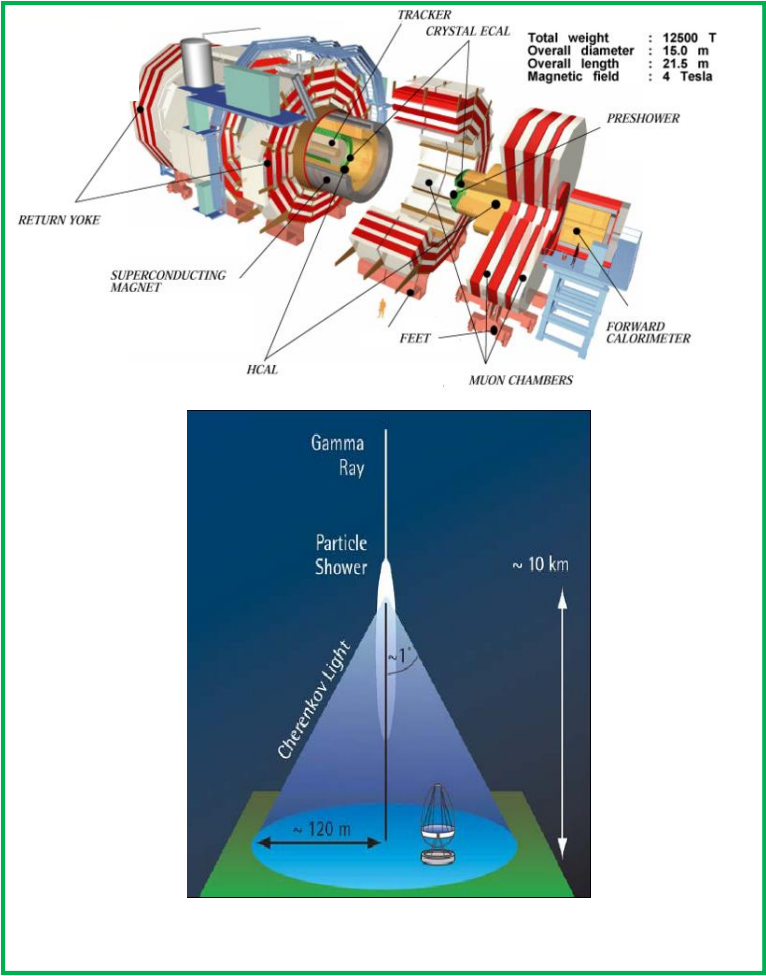
什么是硅光电倍增器 (SiPM)

- 硅光电倍增器 (SiPM--silicon photomultiplier)是一种由工作于雪崩击穿电压之上和具有雪崩淬灭机制的单光子雪崩二极管 (SPAD) 阵列并联构成的，具有极佳的光子数分辨和单光子探测灵敏度的硅基弱光探测器。

SiPM $\approx$ SPAD Array

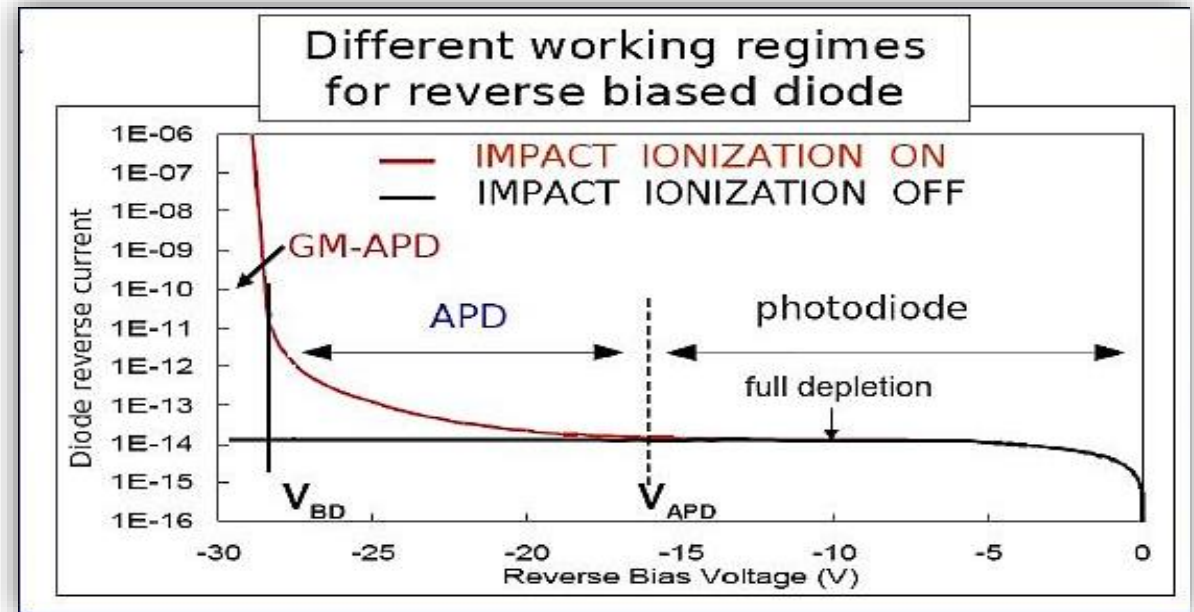
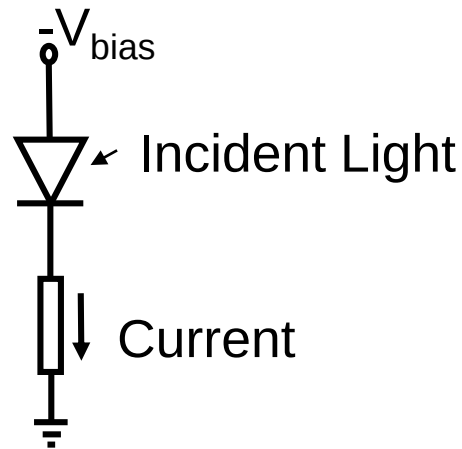
- 关键词：硅光电探测器、雪崩光电二极管 (APD) 阵列、雪崩淬灭、“盖革”模式 (Geiger mode)，光子数分辨、单光子探测

SiPM兴起于上个世纪九十年代，在粒子物理与核物理研究、核医学诊疗、激光雷达、荧光检测领域有有非常重要和广泛的应用



Avalanche Photodiode and Operating Modes

Photodiode



Photodiode

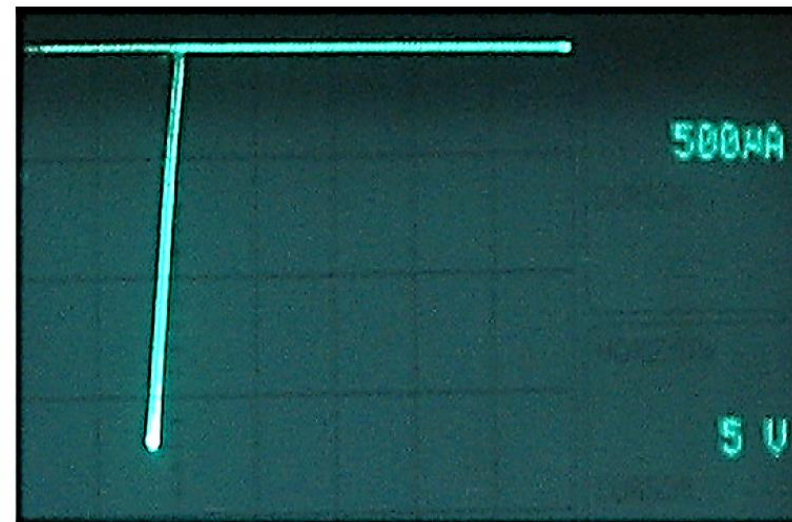
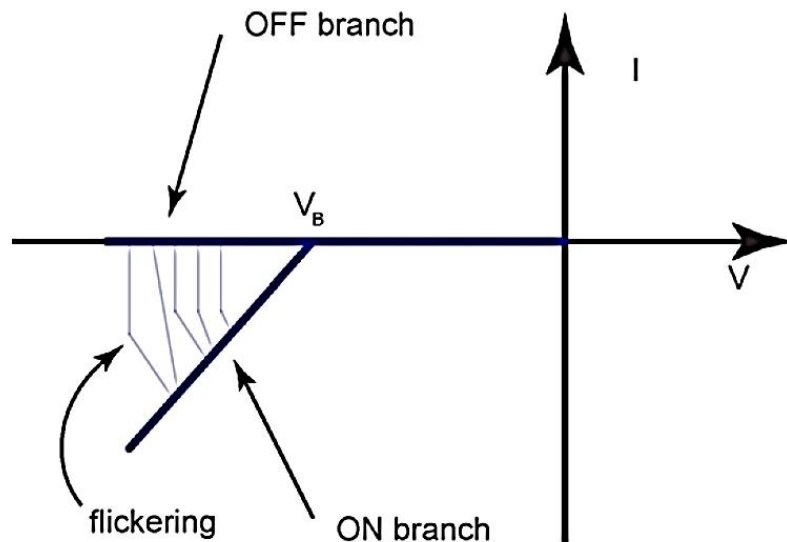
- $0 < V < V_{APD}$
- $G=1$
- Operate at high light level (hundreds of photons)

APD

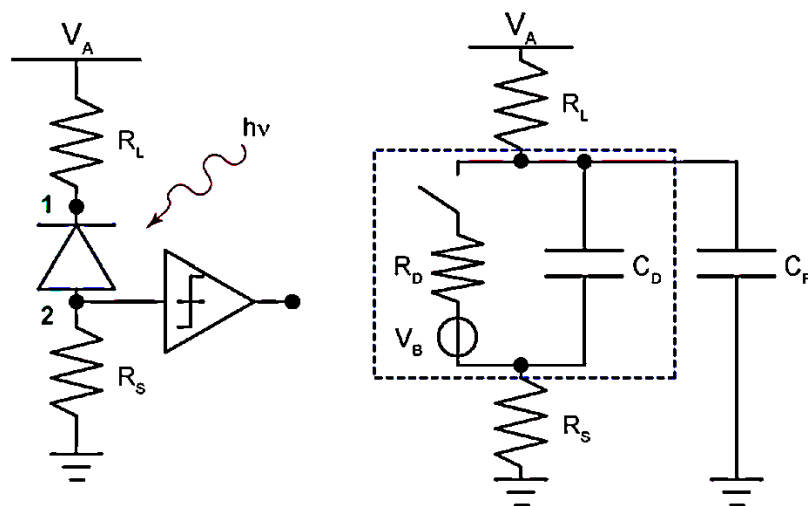
- $V_{APD} < V < V_{BD}$
- $G = M (10 - 100)$
- Linear mode
- >20 photons detection

G-APD

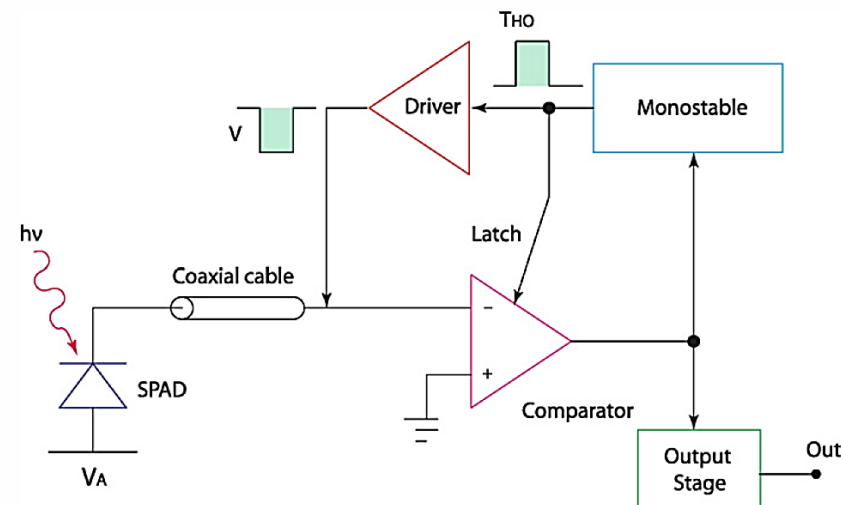
- $V > V_{BD}$
- $G = 10^5 - 10^7$
- Geiger mode
- Single photon detection



I-V characteristic for a reverse biased SPAD with $10\mu\text{m}$ diameter and $\sim 25\text{V}$ breakdown voltage, in dark (*F. Zappa et al. / Sensors and Actuators A 140 (2007) 103–112*)



Passive Quenching



Active Quenching

半导体的雪崩击穿与淬灭机理早在上个世纪60年代研究等离子体微区不稳效应时建立起来

Passive Quenching: tread-off τ_{quench} VS τ_{recovery}

If R_Q is high enough the internal current is so low that statistical fluctuations may quench the avalanche

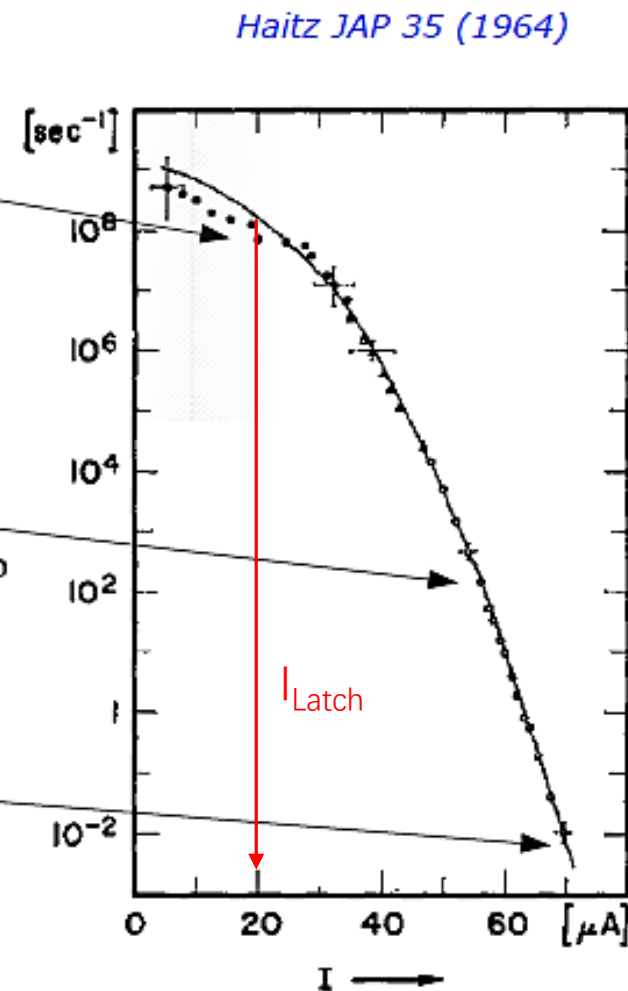
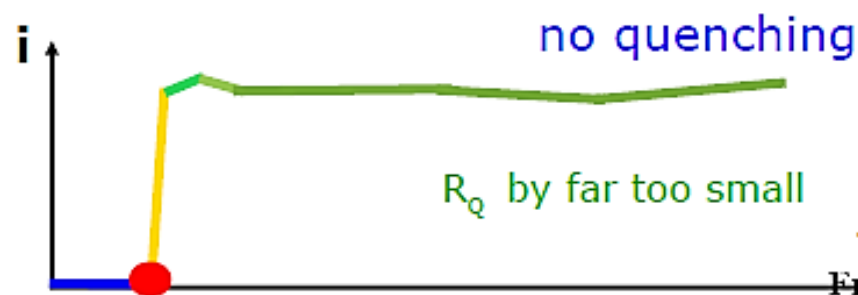
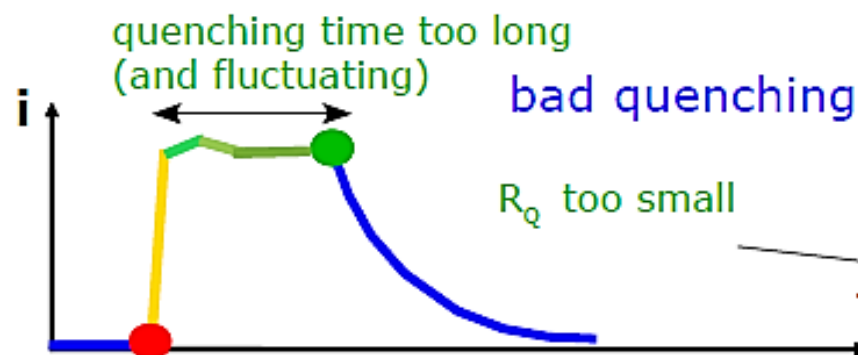
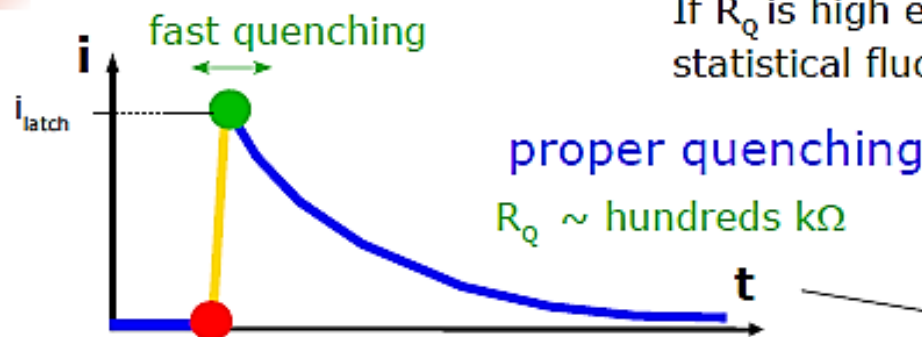
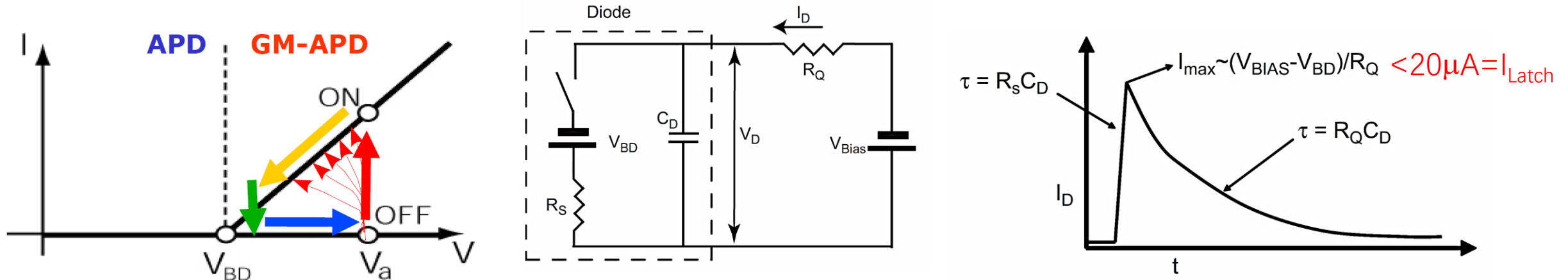


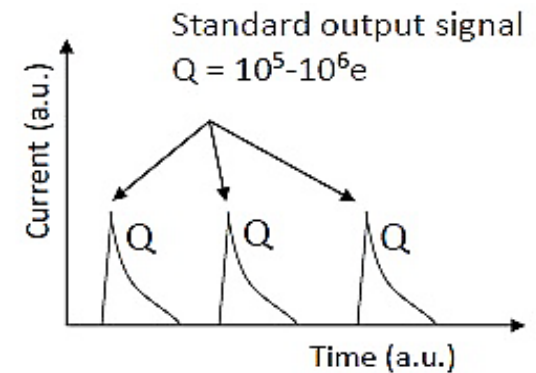
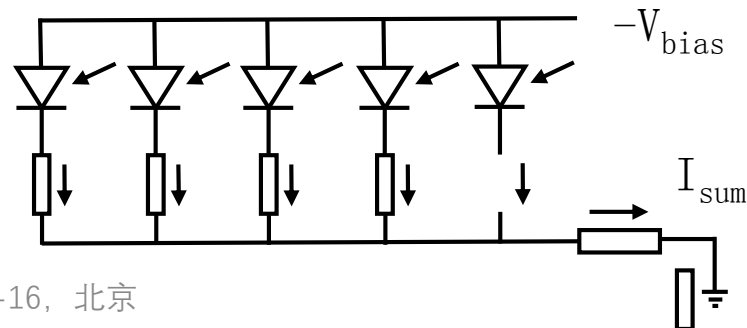
FIG. 2. Turnoff probability per second as function of pulse cu

Passive Quenching G-APD



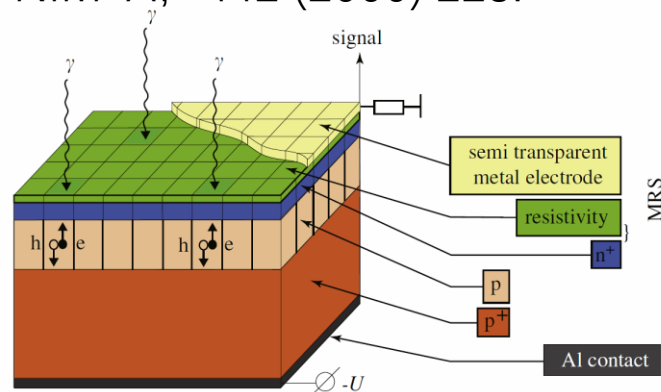
- ON condition: avalanche triggered, switch closed, C_D discharges to V_{BD} with a time constant $R_s C_D$ (discharge time), at the same time the external current asymptotic grows to $(V_{bias} - V_{bd}) / (R_Q + R_d)$
- OFF condition: avalanche quenched, switch open, capacitance charged until no current flowing. From V_{BD} to V_{Bias} with time constant $R_Q C_D$ (recovery time)

GAPD Array – SiPM
Sum Individual Pixels



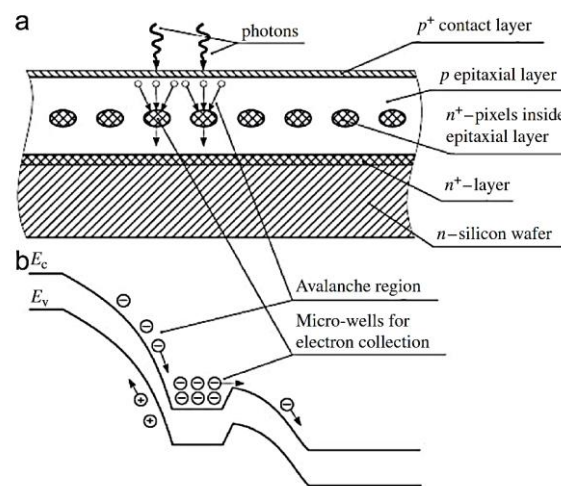
有代表性的SiPM结构 (1)

Russian CPTA, V. Golovin, Patent No. RU 2142175, 1998. ; Z. Sadygov, Patent No. RU 2102820, 1998 ; V. Saveliev, V. Golovin, NIM-A, 442 (2000) 223.



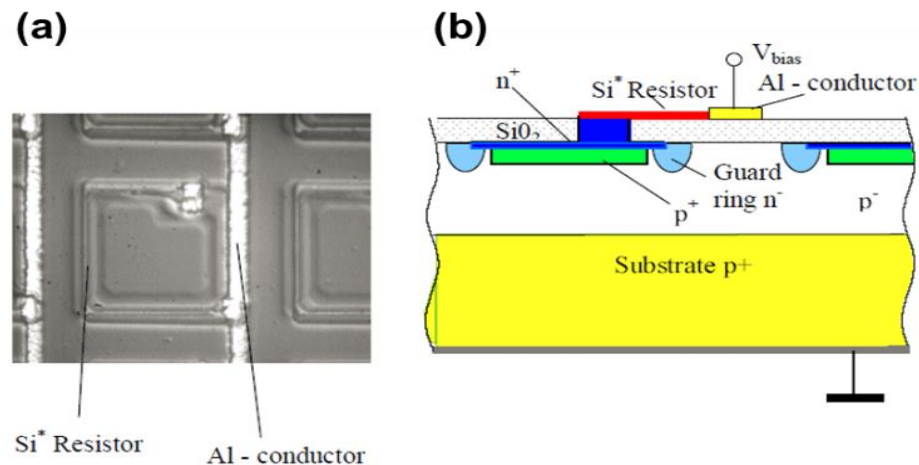
1989-1990 MRS 结构，采用 SiC 或者 SiXOY 做淬灭电阻，半透明金属 Ti 做电极

Z. Sadygov – JINR/Micron (Dubna)-*NIMA 567 (2006)70*



2002 Avalanche Micro-channel/pixel Photo Diodes (AMPD),

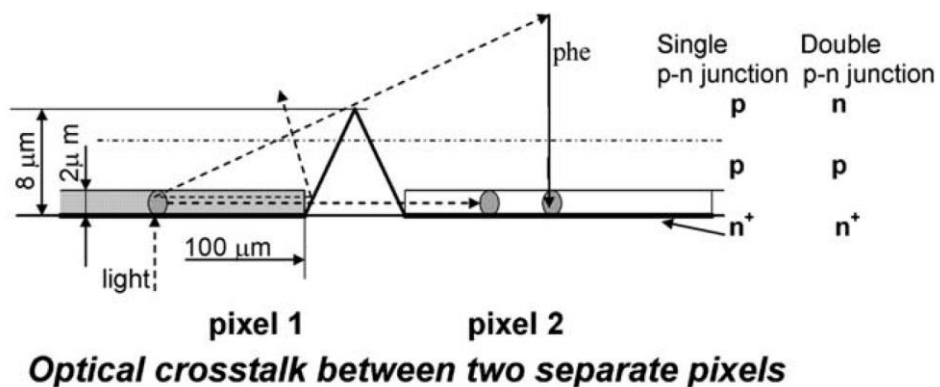
Russian MePhi/Pulsar, Dolgoshein, NIMA 563 (2006)



2002 表面多晶硅淬灭电阻条结构

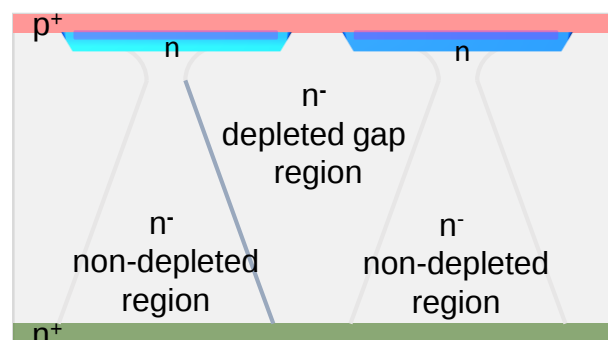
有代表性的SiPM结构 (2)

Russian MePhi/Pulsar ,P.Buzhan,
B.Dolgoshein, NIM-A610
(2009)131–134



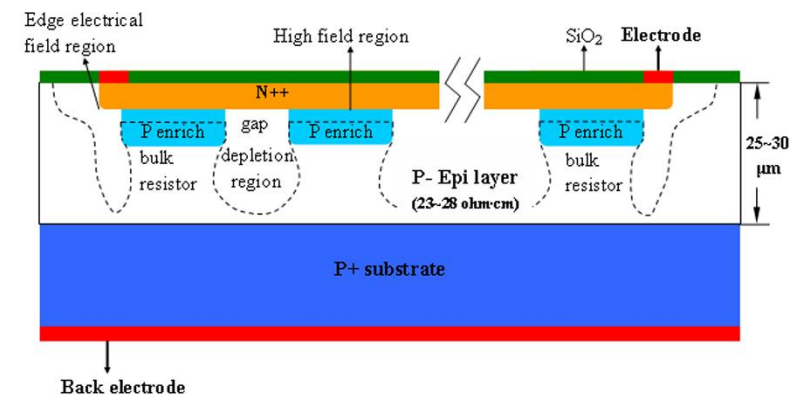
2009 微单元间采用沟槽隔离结构,

Germany MPI, Ninkovic et al
NIM A610 (2009) 142



2009 体硅电阻淬灭SiPM

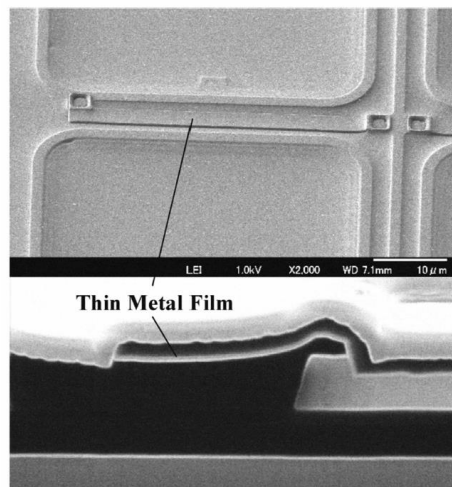
中国 **NDL**, NIM A621 (2010)
116-120



2010 外延电阻淬灭 (EQR)
SiPM, 兼顾高探测效率和大
动态范围

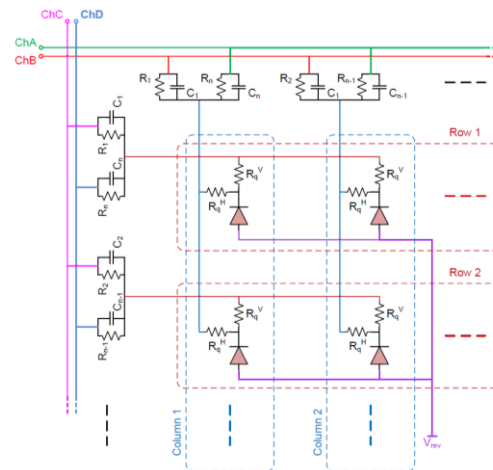
有代表性的SiPM结构 (3)

日本滨松, T. Nagano, et al., 2011
IEEE Nuclear Science Symposium,
NP5.S-130



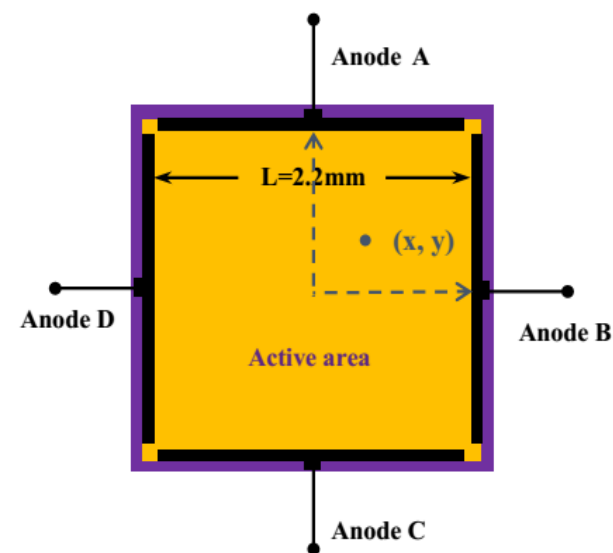
2011 用金属条做淬灭电阻,

Gola A, et al., 2013 IEEE
Nuclear Science Symposium
Conference Record



2013 位置灵敏 SiPM
(LG-SiPM)

中国 **NDL**, IEEE TRANS.
ON ELECTRON DEVICES,
61(2014)3229-3232



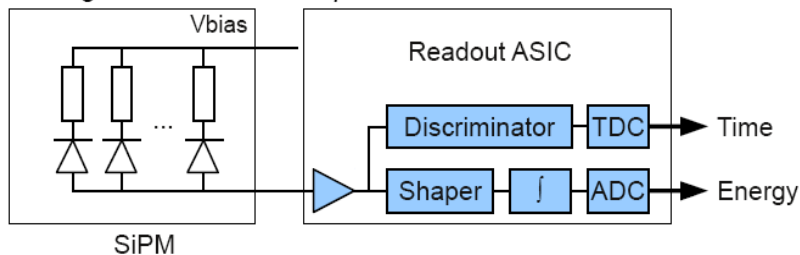
2014 位置灵敏SiPM, 结构简单, 位置和时间分辨率高、读出通道少

Philips, dSiPM, IEEE Nuclear Science Symposium/Medical Imaging Conference,
Orlando, FL, Oct.28, 2009

Analog SiPM

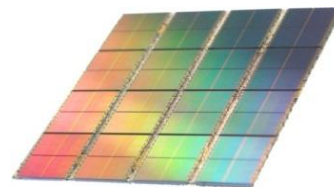


Analog Silicon Photomultiplier Detector

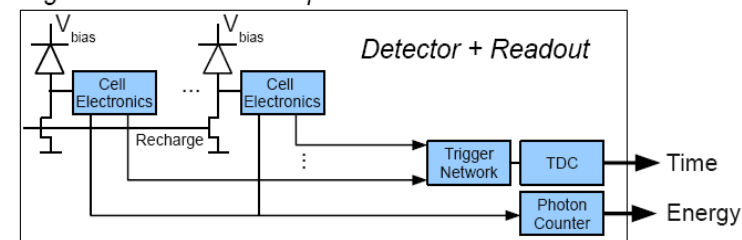


- discrete, limited integration
- analog signals to be digitized
- dedicated ASIC needed
- not scalable

Digital SiPM

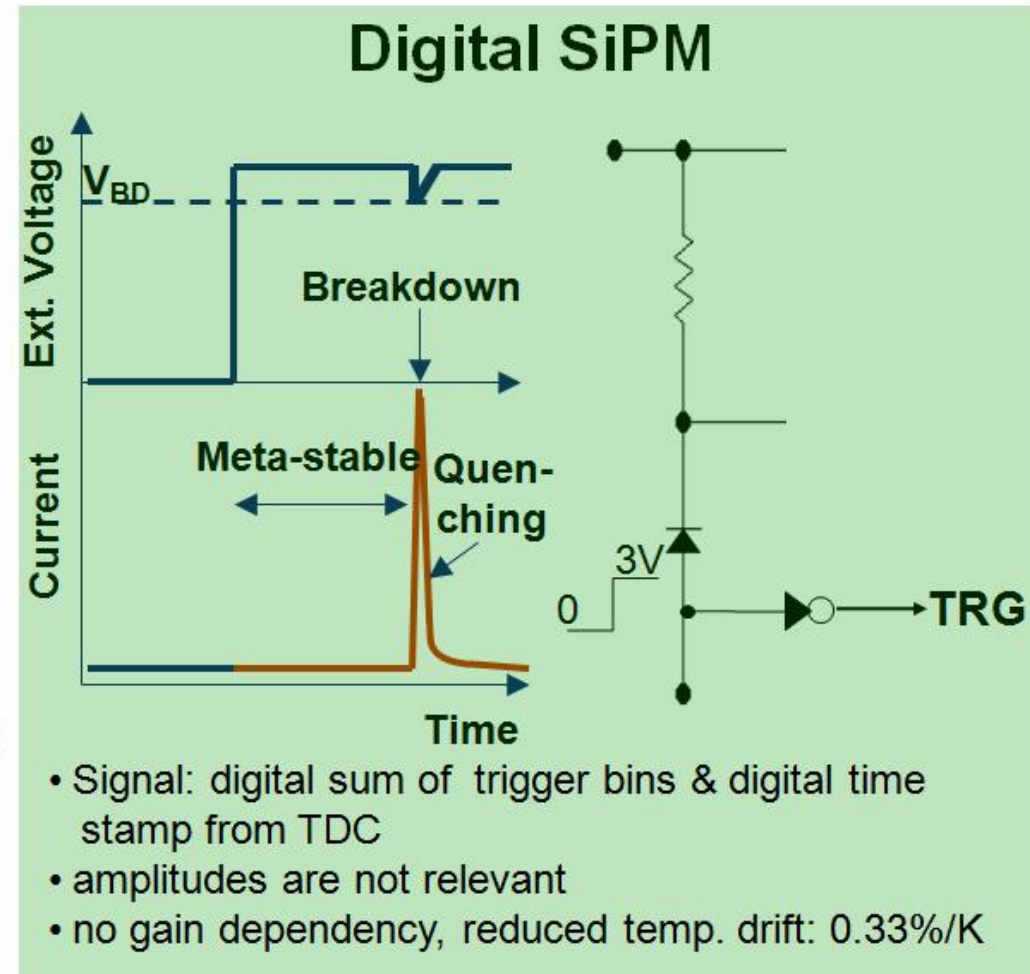
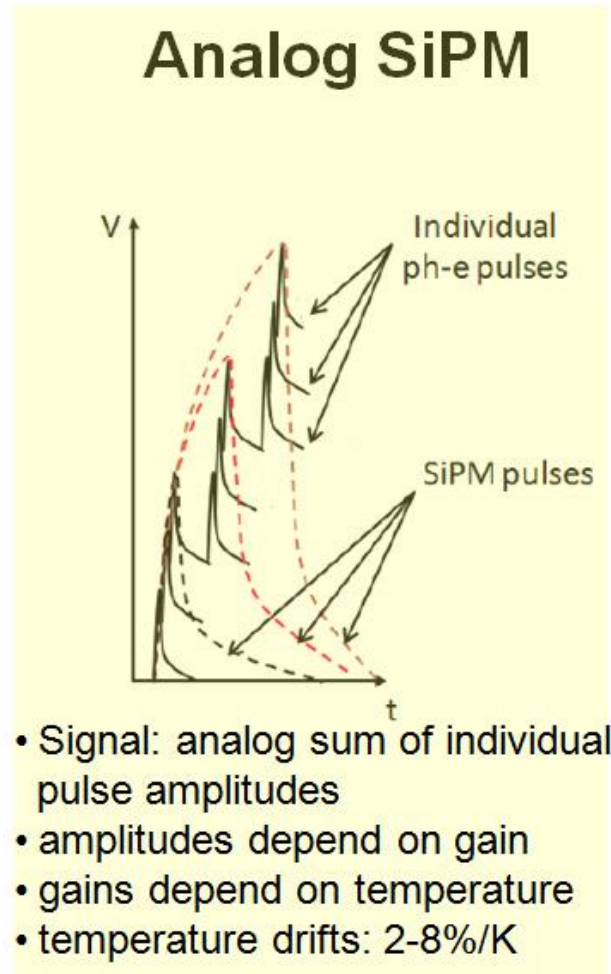


Digital Silicon Photomultiplier Detector



- fully integrated
- fully digital signals
- no ASIC needed
- fully scalable

The dSiPM Takes Advantage of the Binary Nature



“Therefore, while the APD is a linear amplifier for the input optical signal with limited gain, the SPAD is a trigger device so **the gain concept is meaningless.**” *(source: Wikipedia)*

研发SiPM的主要机构



Fabio Acerbi, "SiPM overview: status and trends", 2018 International Workshop on New Photon-Detectors PD18